RENESAS

RL78/I1A

RENESAS MCU

Datasheet

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True Low Power Platform, High Resolution PWM and Rich Analog, 2.7 V to 5.5 V operation, 32 to 64 Kbyte Flash, for Inverter Control, Digital Power Control and Lighting Control Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology

- 2.7 V to 5.5 V operation from a single supply
- Stop (RAM retained): 0.23 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.60 μA
- Operating: 156.25 µA/MHz

16-bit RL78 CPU Core

- Delivers 41 DMIPS at maximum operating frequency of 32 MHz
- Instruction execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC architecture (Harvard) with 3-stage pipeline
- Multiply signed & unsigned: 16 x 16 to 32-bit result in 1 clock cycle
- MAC: 16 x 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Main Flash Memory

- Density: 32 KB to 64 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory

- Data flash with background operation
- Data flash size: 4 KB
- Erase cycles: 1 million (typ.)
- Erase/programming voltage: 2.7 V to 5.5 V

RAM

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- 2 KB to 4 KB size options
- · Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator

- 32 MHz with +/- 1% accuracy over voltage (2.7 V to 5.5 V) and temperature (-20°C to 85°C)
- Pre-configured settings: 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz & 1 MHz

Reset and Supply Management

- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 6 setting options (Interrupt and/or reset function)

Data Memory Access (DMA) Controller

- Up to 2 fully programmable channels
- Transfer unit: 8- or 16-bit

16-bit timers KB0 to KB2, and KC0 for PWM output

16-bit timers KB0 to KB2: maximum 6 outputs (3 channels \times 2)

- Smooth start function, dithering function, forced output stop function (unsynchronized with comparator or external interrupt) enables over-voltage protection, over-current protection and peak current control, and single/interleave PFC function
- Average resolution < 0.98 nsec output, 64 MHz (when using PLL) + dithering option
- 16-bit timer KC0 (1 channel × 6 (output))
- PWM output gating function by interlocking with 16-bit timers KB0, KB1, and KB2

Extended-Function Timers

- Multi-function 16-bit timers: Up to 8 channels
- Real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- Interval timer: 12-bit, 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Multiple Communication Interfaces

- Up to 1 channel x I²C multi-master (SMBus/PMBus support)
- Up to 1 channel x Simplified SPI (CSINote1)/SPI (7-, 8bit)
- Up to 3 channels x UART (7-, 8-, 9-bit), DALI support 1 channel (8-, 16-, 17-, 24-bit, master and slave)
- Up to 1 channel x LIN

Rich Analog

- ADC: Up to 11 channels, 8/10-bit resolution, 2.125 $\mu \rm s$ conversion time
- Supports 2.7 V
- Internal voltage reference (1.45 V)
- Comparator: High response time 70 ns (typ.), up to 6 channels, internal DAC 3 channels 8-bit resolution, window comparator mode
- PGA (x4 to x32): 6 input channels
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)

- Flash memory CRC calculation
- RAM parity error check
- RAM/SFR write protection
- Illegal memory access detection
- Clock stop/frequency detection
- ADC self-test

General Purpose I/O

- 5-V tolerant, high-current (up to 8.5 mA per pin)
- Open-drain, internal pull-up support

Operating Ambient Temperature

- Standard: –40°C to +105°C
- Extend: -40°C to +125°C

Package Type and Pin Count

SSOP: 20, 30, 38



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Notes 1. Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/I1A				
			20 pins	30 pins	38 pins		
64 KB	4 KB	4 KB ^{Note}	-	R5F107AE	R5F107DE		
32 KB	4 KB	2 KB	R5F1076C	R5F107AC	-		

Note This is about 3 KB when the self-programming function and data flash function are used.



1.2 List of Part Numbers



Figure 1-1. Part Number, Memory Size, and Package of RL78/I1A

Pin count	Package	Operating Ambient Temperature	Part Number
20 pins	20-pin plastic LSSOP	TA = -40 to +105°C	R5F1076CGSP#V0, R5F1076CGSP#X0
(4.4 × 6.5)	TA = -40 to +125°C	R5F1076CMSP#V0, R5F1076CMSP#X0	
30 pins	30-pin plastic LSSOP (7.62 mm (300))	TA = -40 to +105°C	R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0
		TA = -40 to +125°C	R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0
38 pins	38-pin plastic SSOP	TA = -40 to +105°C	R5F107DEGSP#V0, R5F107DEGSP#X0
	(7.62 mm (300))	TA = -40 to +125°C	R5F107DEMSP#V0, R5F107DEMSP#X0

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (4.4 x 6.5)





Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
- **3.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).



1.3.2 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.3.3 38-pin products

• 38-pin plastic SSOP (7.62 mm (300))



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.4 Pin Identification

ANI0 to ANI2,		REGC:	Regulator Capacitance
ANI4 to ANI7,		RESET:	Reset
ANI16 to ANI19:	Analog Input	RTC1HZ:	Real-time Clock Correction Clock
AVREFM:	Analog Reference Voltage Minus		(1 Hz) Output
AVREFP:	Analog Reference Voltage Plus	RxD0, RxD1,	
CMP0P to CMP5P:	Comparator Analog Input	DALIRxD4:	Receive Data
CMPCOM:	Comparator External Reference	SCK00:	Serial Clock Input/Output
	Voltage	SCLA0:	Serial Clock Input/Output
EXCLK:	External Clock Input (Main System	SDAA0:	Serial Data Input/Output
	Clock)	SI00:	Serial Data Input
EXCLKS:	External Clock Input (Subsystem	SO00:	Serial Data Output
	Clock)	TI03, TI05, TI06,	
INTP0, INTP3,		TI07:	Timer Input
INTP4, INTP9,		TO03, TO05, TO06,	
INTP10, INTP11,		TKBO00, TKBO01 to	0
INTP20 to INTP23:	Interrupt Request from Peripheral	TKBO20, TKBO21,	
P02, P03,		TKCO00 to TKCO05	5: Timer Output
P05, P06:	Port 0	TOOL0:	Data Input/Output for Tool
P10 to P12:	Port 1	TxRx4:	Serial Data Input/Output for Single
P20 to P22,			Wired UART
P24 to P27:	Port 2	TxD0, TxD1	
P30, P31:	Port 3	DALITxD4:	Transmit Data
P40:	Port 4	Vdd:	Power Supply
P75 to P77:	Port 7	Vss:	Ground
P120 to P124:	Port 12	X1, X2:	Crystal Oscillator (Main System Clock)
P137:	Port 13	XT1, XT2:	Crystal Oscillator (Subsystem Clock)
P147:	Port 14		
P200 to P206:	Port 20		



1.5 Block Diagram

1.5.1 20-pin products



- Remarks 1. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.
 - **2.** The shared function CMP3P can be assigned to P147 by setting the CMPSEL0 bit in the comparator input switch control register (CMPSEL).



1.5.2 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.

1.5.3 38-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR1) or the input switch control register (ISC). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR1) and Figure 15-20 Format of Input Switch Control Register (ISC) in the RL78/I1A User's Manual.



1.6 Outline of Functions

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR1) is set to 00H.

					(1/3)			
	Item	20-pin	30)-pin	38-pin			
		R5F1076C	R5F107AC	R5F107AE	R5F107DE			
Code flash m	emory (KB)	32	32	64	64			
Data flash me	emory (KB)	4	4	4	4			
RAM (KB)		2	2	2 4 ^{Note 1} 4 ^{Note 1}				
Address spac	e	1 MB						
Main system clock	High-speed system clock	HS (High-speed main)	cillation, external main s mode: 1 to 20 MHz (Vpp node: 1 to 8 MHz (Vpp	,				
	High-speed on-chip oscillator	HS (High-speed main) r LS (Low-speed main) m						
Clock for 16-b and KC0	bit timers KB0 to KB2,	64 MHz (TYP.)						
Subsystem cl only)	ock (38-pin products	XT1 (crystal) oscillation 32.768 kHz	, external subsystem clo	ck input (EXCLKS)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)						
General-purp	ose register	(8-bit register \times 8) \times 4 banks						
Minimum inst	ruction execution time	0.03125 μ s (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)						
		0.05 μ s (High-speed sy	stem clock: f _{MX} = 20 MH	z operation)				
		30.5 μ s (Subsystem clo	оск: fsuв = 32.768 kHz ор	peration) (38-pin products o	nly)			
Instruction se	t	 8-bit operation, 16-bit Multiplication (8 bits > Bit manipulation (Set) 	-	n operation), etc.				
I/O port	Total	16		26	34			
	CMOS I/O	13		23	29			
	CMOS input	3		3	5			
	CMOS output	-		_	_			
Timer	16-bit timer TAU	8 channels (no timer output)	8 channels (timer outpu	it: 1, PWM output: 1 ^{Note 2})	8 channels (timer outputs: 3, PWM outputs: 3 ^{Note 2})			
	16-bit timer KB	2 channels (PWM outputs: 4)	3	channels (PWM outputs: 6				
	16-bit timer KC	1 channel (PWM outputs: 3)	1 channel (PWM outputs: 6)					

Notes 1. This is about 3 KB when the self-programming function and data flash function are used. (For details, see CHAPTER 3 in the RL78/I1A User's Manual.)

The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/I1A User's Manual).



	Item	20 pip	20 nin	(2/3)				
	nem	20-pin R5F1076C	30-pin	38-pin R5F107DE				
- .		I	R5F107AC, R5F107AE	ROF 107DE				
Timer	Watchdog timer		1 channel					
-	Real-time clock (RTC)		1 channel ^{Notes 1, 2}					
	12-bit interval tir (IT)	ner	1 channel					
	RTC output		– 1 1 fsi					
8/10-bit resolut	tion A/D converte	er 6 channels	11 channels	11 channels				
Comparator		4 channels	6 channels	6 channels				
Programmable	gain amplifier		1 channel					
	Inpu	t ^{Note 3} 4 channels	6 channels	6 channels				
Serial interface)	[20-pin] Note 5						
			bus and DMX512): 1 channel					
			l communication): 1 channel					
		[30-pin products]	,					
			bus and DMX512): 1 channel					
		UART: 1 channel	- ,					
			I communication): 1 channel					
		[38-pin products]						
			channel/UART (Supporting LIN-bus and D	MX512) [.] 1 channel				
		UART: 1 channel						
		UART (Supporting DAL	I communication): 1 channel					
	I ² C bus	1 channel	1 channel	1 channel				
Multiplier and c accumulator	divider/multiply-	• 32 bits ÷ 32 bits = 32 bit	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 					
DMA controller	•		2 channels					
Vectored interr	upt Internal	27	30	30				
sources	External	7	10	11				
Reset	I	Reset by RESET pin						
		 Internal reset by watched 	dog timer					
		 Internal reset by power- 						
		Internal reset by voltage						
		Internal reset by illegal						
		 Internal reset by RAM p 	barity error					

Notes 1. The subsystem clock (fsub) can be selected as the operating clock only for 38-pin products.

2. The 20- and 30-pin products can only be used as the constant-period interrupt function.

- 3. The comparator input is alternatively used with analog input pin (ANI pin).
- The illegal instruction is generated when instruction code FFH is executed. Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or onchip debug emulator.
- 5. The 20 pin products can only be used 1 UART simultaneously due to sharing of the same I/O pins.



			(3/3)			
Item	20-pin	30-pin	38-pin			
	R5F1076C	R5F107AC, R5F107AE	R5F107DE			
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)				
Voltage detector		V to 4.06 V (6 stages) V to 3.98 V (6 stages)				
On-chip debug function	Provided					
Power supply voltage	V _{DD} = 2.7 to 5.5 V					
Operating ambient temperature	T _A = -40 to +105°C (G:	$T_A = -40$ to +105°C (G: Industrial applications), $T_A = -40$ to +125°C (M: Industrial applications)				



2. ELECTRICAL SPECIFICATIONS (G: Industrial applications, $T_A = -40$ to +105°C)

In this chapter, shows the electrical specifications of the target products. Target products (G: Industrial applications): $T_A = -40$ to $+105^{\circ}C$ R5F107xxGxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.



2.1 Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		–0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V_{DD} +0.3 $^{\text{Note 1}}$	V
Input voltage	Vi1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Vaii	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

Absolute Maximum Ratings (T_A = 25°C) (1/2)

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - 2. AV_{REF (+)}: + side reference voltage of the A/D converter.
 - **3.** Vss: Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40 -70 -100 -0.5 -2 40 70	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		–170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins	P02, P03, P40, P120	70	mA
		170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	IOL2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (T_A = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/crystal resonator		1.0		20.0	MHz
XT1 clock oscillation frequency $(f_{XT})^{Note}$	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.



2.2.2 On-chip oscillator characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracy ^{Note 2}		T _A = -20 to 85°C	-1		+1	%
		T _A = -40 to 105°C	-1.5		+1.5	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.

2.2.3 PLL characteristics

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f_{MX} = 4 MHz)	3.94	4.00	4.06	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f_{IH} = 4 MHz)	3.94	4.00	4.06	MHz
PLL output clock frequency ^{Note}	fpll			$f_{\text{PLLIN}} imes 16$		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-1.0	mA
	Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-12.0	mA	
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-4.0	mA
		Total of P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{Note 3}$) Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-30.0	mA
			$2.7~V \leq V_{\text{DD}} < 4.0~V$			-10.0	mA
			$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-30.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-14.0	mA
Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA	
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.7	mA

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.

3. Specification under conditions where the duty factor \leq 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated

with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (Iон × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	IOL1	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			8.5 ^{Note 2}	mA
IOW ^{Note 1}		P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			1.5 ^{Note 2}	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			7.5	mA
		Total of P05, P06, P10 to P12, P30,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		P31, P75 to P77, P147, P200 to P206 (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} < 4.0~V$			17.5	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			80.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			25.0	mA
	IOL2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			2.8	mA

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	2.1		Vdd	V
			TTL input buffer $3.3~V \leq V_{\text{DD}} < 4.0~V$	2.0		Vdd	V
			TTL input buffer $2.7 \ V \leq V_{\text{DD}} < 3.3 \ V$	1.5		Vdd	V
Input voltage, low	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	VIL2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	V
			TTL input buffer $2.7 \ V \leq V_{\text{DD}} < 3.3 \ V$	0		0.32	V

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Caution The maximum value of V ${\mbox{\tiny H}}$ of pins P02, P10 to P12 is V ${\mbox{\tiny DD}},$ even in the N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ mA \end{array} \label{eq:DD}$	$V_{\text{DD}}-0.7$			V
		P200 to P206	$\begin{array}{l} 2.7 \ \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \ \text{V}, \\ \text{I}_{\text{OH1}} = -1.0 \ \text{mA} \end{array}$	$V_{\text{DD}}-0.5$			V
	Vон2	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh2 = -100 μ A	$V_{\text{DD}}-0.5$			V
Output voltage, low	Vol1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:DD}$			0.7	V
		P200 to P206	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 4.0 \ mA \end{array} \label{eq:DD}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 1.5 mA			0.4	V
	Vol2	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol2 = 400 μ A			0.4	V

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ilih1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = VDD				1	μA
	ILIH2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	IL1L1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = Vss				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	Vı = Vss, Ir	i input port	10	20	100	kΩ

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)



2.3.2 Supply current characteristics

$(T_{A} = -40 \text{ to})$	+105°C. 2	2.7 V < Vpr	< 5.5 V.	Vss = 0 V) (1/2)	
117 40 10	· 100 0, 2		· _ •.• •,	•••••••••••••••••••••••••••••••••••••••	

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	fı⊣ = 32 MHz ^{Note 3}	V _{DD} = 5.0 V		5.0	7.5	mA
CURRENT Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		5.0	7.5	mA
			mode	fi⊢ = 24 MHz ^{Note 3}	V _{DD} = 5.0 V		3.9	5.8	mA
					V _{DD} = 3.0 V		3.9	5.8	mA
				f⊮ = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.2	mA
					V _{DD} = 3.0 V		2.9	4.2	mA
			LS (low- speed main) mode ^{Note 5}	$f_{H} = 8 \text{ MHz}^{\text{Note 3}},$ TA = -40 to + 85°C	V _{DD} = 3.0 V		1.3	2.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.0	mA
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	4.9	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.0	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA
				V _{DD} = 5.0 V	Resonator connection		2.0	2.9	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	2.9	mA
				V _{DD} = 3.0 V	Resonator connection		2.0	2.9	mA
			LS (low-	speed main) $V_{DD} = 3.0 V$, mode ^{Note 5} $T_A = -40$ to + 85°C	Square wave input		1.2	1.8	mA
			speed main) mode ^{Note 5}		Resonator connection		1.2	1.8	mA
			HS (high-	f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		5.4	8.5	mA
			speed main) mode ^{Note 5}	fpll = 64 MHz, fclк = 32 MHz	V _{DD} = 3.0 V		5.4	8.5	mA
			mode	f _{IH} = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	5.7	mA
				fpll = 64 MHz, fclк = 16 MHz	V _{DD} = 3.0 V		3.3	5.7	mA
			Subsystem	fsuв = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA
			clock operation	T _A = -40°C	Resonator connection		4.4	6.2	μA
			operation	fsuв = 32.768 kHz ^{Note 4}	Square wave input		4.2	6.0	μA
				T _A = +25°C	Resonator connection		4.4	6.2	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μA
				T _A = +50°C	Resonator connection		4.5	7.4	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA
				T _A = +70°C	Resonator connection		4.6	8.3	μA
				fsuв = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA
				T _A = +85°C	Resonator connection		5.4	11.6	μA
				fsuв = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA
				T _A = +105°C	Resonator connection		7.1	21.0	μA

(Notes and Remarks are listed on the next page.)



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- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), and LS (low-speed main) modes
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.

• The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten. In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into

- the RTC.
- 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- 3. When high-speed system clock and subsystem clock are stopped.
- 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}_{@}1 \text{ MHz}$ to 32 MHz
 - LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 8 MHz
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. file: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$ (2/2)

Parameter	Symbol			Conditions	1	MIN.	TYP.	MAX.	Uni
Supply	IDD2 ^{Note 2}	HALT	HS (high-	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.72	2.9	mA
Current Note 1		mode	speed main) mode ^{Note 6}		V _{DD} = 3.0 V		0.72	2.9	mA
			mode	f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.57	2.3	mA
					V _{DD} = 3.0 V		0.57	2.3	mA
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	1.7	mA
					V _{DD} = 3.0 V		0.50	1.7	mA
			LS (low- speed main) mode ^{Note 6}	$f_{IH} = 8 \text{ MHz}^{Note 4},$ $T_A = -40 \text{ to } +85^{\circ}\text{C}$	V _{DD} = 3.0 V		320	910	μA
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	m/
			speed main)	V _{DD} = 5.0 V	Resonator connection		0.50	2.0	m
			mode ^{Note 6}	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.40	1.9	m/
				V _{DD} = 3.0 V	Resonator connection		0.50	2.0	m
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	m
				V _{DD} = 5.0 V	Resonator connection		0.30	1.08	m
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.24	1.02	m
				V _{DD} = 3.0 V	Resonator connection		0.30	1.08	m
			LS (low-	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		130	720	μ
			. ,	V _{DD} = 3.0 V, T _A = -40 to +85°C	Resonator connection		170	760	μ
			HS (high-	fpll = 64 MHz, fclk = 32 MHz	V _{DD} = 5.0 V		1.15	4.0	m
			speed main)		V _{DD} = 3.0 V		1.15	4.0	m
			mode ^{Note 6}		V _{DD} = 5.0 V		0.95	3.2	m
				fpll = 64 MHz, fclk = 16 MHz	V _{DD} = 3.0 V		0.95	3.2	m
			Subsystem	fsue = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.70	μ
			clock	T _A = -40°C	Resonator connection		0.47	0.89	μ
			operation	fsue = 32.768 kHz ^{Note 5}	Square wave input		0.33	0.70	μ
				T _A = +25°C	Resonator connection		0.52	0.89	μ
				fsue = 32.768 kHz ^{Note 5}	Square wave input		0.41	1.90	μ
				T _A = +50°C	Resonator connection		0.60	2.09	μ
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.54	2.80	μ
				T _A = +70°C	Resonator connection		0.73	2.99	μ
				fs∪в = 32.768 kHz ^{Note 5}	Square wave input		1.27	6.10	μ
				T _A = +85°C	Resonator connection		1.46	6.29	μ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.04	15.5	μ
				T _A = +105°C	Resonator connection		3.23	15.7	μ
	IDD3	STOP	T _A = -40°C				0.18	0.50	μ
		mode	$T_{A} = +25^{\circ}C$ $T_{A} = +50^{\circ}C$				0.23	0.50	μ
		Note 7					0.27	1.70	μ
			T _A = +70°C				0.44	2.60	μ
			T _A = +85°C				1.17	5.90	μ
			T _A = +105°C				2.94	15.3	μ

(Notes and Remarks are listed on the next page.)



the RTC.

- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main) and LS (low-speed main) modes.
 - •The currents in the "TYP." column do not include the operating currents of the peripheral modules.
- <R> •The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten. In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- 4. When high-speed system clock and subsystem clock are stopped.
- **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz
 - LS (low-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 8 MHz
- 7. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions					MAX.	Unit
Low-speed on- chip oscillator operating current	_{FIL} Note 1						0.20		μA
RTC operating current	IRTC Notes 1, 2, 3						0.02		μA
12-bit interval timer operating current	lıT Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	WDT Notes 1, 2, 5	f⊩ = 15 kHz					0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion maximum speed			$AV_{REFP} = V_{DD} = 5.0 V$ node, $AV_{REFP} = V_{DD} = 3.0 V$		1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	ADREF ^{Note 1}						75.0		μA
Temperature sensor operating current	ITMPS ^{Note 1}						75.0		μA
LVD operating current	LVD ^{Notes 1, 7}						0.08		μA
Self- programming operating current	IFSP ^{Notes 1, 8}						2.50	12.2	mA
Programmable gain amplifier operating current	PGA ^{Note 9}				$AV_{REFP} = V_{DD} = 5.0 V$ $AV_{REFP} = V_{DD} = 3.0 V$		0.21 0.18	0.31 0.29	mA mA
Comparator	ICMP ^{Note 10}	When one comp	parator	channel is	$AV_{REFP} = V_{DD} = 5.0 V$		41.4	62	μA
operating current		operating			$AV_{REFP} = V_{DD} = 3.0 V$		37.2	59	μA
	IVREF	When one interr		erence voltage	AV _{REFP} = V _{DD} = 5.0 V		14.8	26	μA
		circuit is operation	ng		$AV_{REFP} = V_{DD} = 3.0 V$		8.9	20	μA
Programmable gain amplifier/ comparator reference current source	I _{IREF} Note 11				$AV_{REFP} = V_{DD} = 5.0 V$ $AV_{REFP} = V_{DD} = 3.0 V$		3.2 2.9	5.1 4.9	μΑ μΑ
BGO operating current	BGO ^{Note 12}						2.50	12.2	mA
SNOOZE	ISNOZ ^{Note 1}	ADC operation	The r	node is perform	ed ^{Note 13}		0.50	1.1	mA
operating current					operations are performed, $_{EFP} = V_{DD} = 5.0 V$		2.0	3.04	mA
		Simplified SPI (CSI)/U	ART operation			0.70	1.54	mA

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(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to the VDD.

- **2.** When the high-speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and fiL operating current). The current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing during self-programming operation.
- **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
- **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
- **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
- 12. Current flowing only during data flash rewrite.
- 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode .

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

- **2.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- **3.** fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is T_A = 25°C
- **5.** Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AV_{REFP} = V_{DD} = 5.0 V)

$$\begin{split} & \text{ICMP} \times 3 + \text{IVREF} + \text{IPGA} + \text{IREF} \\ &= 41.4 \ [\mu\text{A}] \times 3 + 14.8 \ [\mu\text{A}] \times 1 + 210 \ [\mu\text{A}] + 3.2 \ [\mu\text{A}] \\ &= 352.2 \ [\mu\text{A}] \end{split}$$

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AV_{REFP} = V_{DD} = 5.0 V)

ICMP × 2 + IIREF = 41.4 [μA] × 2 + 3.2 [μA] = 86.0 [μA]

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2.4 AC Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Items	Symbol		Conditio	ns		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсү	Main system	HS (high-spe	eed ma	ain) mode	0.03125		1	μs
instruction execution time)		clock (fmain) operation	LS (low-spee main) mode		$T_{A} = -40 \text{ to } +85^{\circ}\text{C}$	0.125		1	μS
		Subsystem clo	ck (fsuв) ope	eratio	n	28.5	30.5	31.3	μs
		In the self	HS (high-spe	eed ma	ain) mode	0.03125		1	μs
		programming mode	LS (low-spee main) mode		T _A = -40 to +85°C	0.125		1	μS
External system clock frequency	fex					1.0		20.0	MHz
	fexs					32		35	kHz
External system clock input high-	texh, texl					24			ns
level width, low-level width	texns, texls					13.7			μS
TI03, TI05, TI06, TI07 input high- level width, low-level width	tт⊪, tт⊫					2/fмск+10			ns
ТО03, ТО05, ТО06, ТКВО00,	fто	HS (high-spee	d main)	4.0	$V \leq V_{\text{DD}} \leq 5.5 \ V$			8	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to		mode		2.7	$V \le V_{DD}$ < 4.0 V			4	MHz
TKCO05 output frequency (When duty = 50%)		LS (low-speed		4.0	$V \leq V_{\text{DD}} \leq 5.5 ~V$			4	MHz
		mode, $T_A = -40$	0 to +85°C	2.7	$V \le V_{DD}$ < 4.0 V			2	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3, INTP20 to INT	,	TP9 to	o INTP11,	1			μS
RESET low-level width	trsl					10			μs

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



Minimum Instruction Execution Time during Main System Clock Operation





When the high-speed on-chip oscillator clock is selected ___

During self programming _ . _ . When high-speed system clock is selected



TCY vs VDD (LS (low-speed main) mode)

When the high-speed on-chip oscillator clock is selected

--- During self programming When high-speed system clock is selected







2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode) $(T_A = -40 \text{ to } +105^\circ\text{C}, \ 2.7 \text{ V} \le V_{\text{DD}} \le 5.5 \text{ V}, \ \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-s Mo	peed main) ode	· ·	beed main) bde	Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		$2.7 \text{ V} \leq \text{V}_{\text{DD}}$	\leq 5.5 V		fмск/6		f мск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are: HS (high-speed main) mode: 32 MHz (2.7 V \leq V_{DD} \leq 5.5 V) LS (low-speed main) mode: 8 MHz (2.7 V \leq V_{DD} \leq 5.5 V), T_A = -40 to +85°C

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))



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(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions	HS (high-sp	beed main)	LS (low-sp	Unit	
			Мо	de	Мо	de	
			MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tĸcyı ≥ 4/fclĸ	125		500		ns
SCKp high-/low-level	t кн1,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	tксү1/2 – 12		tксү1/2 – 50		ns
width	t ĸ∟1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	tkcy1/2 – 18		tксү1/2 – 50		ns
SIp setup time (to SCKp [↑])	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	44		110		ns
Note 1		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	44		110		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi1		19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

5. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 - g: PIM and POM number (g = 1)
 - 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



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(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t ксү2	$4.0~V \leq V_{DD} \leq 5.5~V$	20 MHz < fмск	8/fмск		-		ns
			fмск \leq 20 MHz	6/fмск		6/fмск		ns
		$2.7~V \leq V_{DD} \leq 5.5~V$	16 MHz < fмск	8/fмск		-		ns
			fмск ≤ 16 MHz	6/fмск		6/f мск		ns
SCKp high-/low- level width	tкн2, tкL2			tксү2/2		tксү2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsik2			1/fмск+20		1/fмск+30		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+31		1/fмск+31		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso2	C = 30 pF ^{Note 4}			2/fмск+ 44		2/fмск+ 110	ns

 $(T_A = -40 \text{ to } +105^{\circ}C^{\text{Note 6}}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - **6.** Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 - n: Channel number (mn = 00))





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Simplified SPI (CSI) mode connection diagram (during communication at same potential)







Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)





2. m: Unit number, n: Channel number (mn = 00)


(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions			HS (high-speed main) Mode		LS (low-speed main) Mode		
						MAX.	MIN.	MAX.		
Transfer		Reception	4.0 V	$\leq V_{\text{DD}} \leq 5.5~\text{V},~2.7~\text{V} \leq V_{\text{b}} \leq 4.0~\text{V}$		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps	
rate		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps			
			2.7 V	\leq V_{DD} < 4.0 V, 2.3 V \leq V_b \leq 2.7 V		fмск/6 ^{Note 1}		fмск/6 ^{Note 1}	bps	
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		5.3		1.3	Mbps			

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLk) are:HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$ LS (low-speed main) mode: $8 \text{ MHz} (2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vbb tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VL, see the DC characteristics with TTL input buffer selected.

- **Remarks 1.** V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2) ($T_A = -40$ to $+105^{\circ}C^{Note 5}$, 2.7 V $\leq V_{DD} \leq 5.5$ V, Vss = 0 V)

Parameter	Symbol		Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V	$\leq V_{\text{DD}} \leq 5.5~V,~2.7~V \leq V_{\text{b}} \leq 4.0~V$		Note 1		Note 1	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V _b = 2.7 V		2.8 ^{Note 2}		2.8 ^{Note 2}	Mbps
			2.7 V	$\leq V_{\text{DD}}$ < 4.0 V, 2.3 V $\leq V_{\text{b}} \leq$ 2.7 V		Note 3		Note 3	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 ^{Note 4}		1.2 ^{Note 4}	Mbps

Notes 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_DD \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- This value as an example is calculated when the conditions described in the "Conditions" column are met. See Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_DD < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = $\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- 5. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03))



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, V_b[V]: Communication line voltage
 2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)



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(5) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}^{\text{Note 3}}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high main) N		LS (low-s main) M	•	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 $\geq 2/f$ ськ		200		1150		ns
			$\label{eq:VDD} \begin{array}{l} 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	300		1150		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	≤ 5.5 V, 2.7 V \leq V _b \leq 4.0 V, R _b = 1.4 kΩ	tксү1/2 – 50		tксү1/2 — 75		ns
		$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < \\ C_{\text{b}} = 30 \ \text{pF}, \end{array} \end{array} \label{eq:VDD}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	tксү1/2 – 120		tксү1/2 – 170		ns
SCKp low-level width	tĸ∟ı	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$		tксү1/2 – 7		tксү1/2 — 50		ns
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF}, \text{ F}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	tксү1/2 – 10		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, Rb = 1.4 k\Omega	81		479		ns
		$2.7 V \le V_{DD} < C_b = 30 pF, F$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	177		479		ns
SIp hold time (from SCKp↑)	tksi1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$\le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ R _b = 1.4 kΩ	10		19		ns
Note 1		$2.7 V \le V_{DD} \le C_b = 30 pF, F$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	10		19		ns
Delay time from SCKp↓ to SOp	tkso1	$4.0 V \le V_{DD} \le C_b = 30 \text{ pF, F}$	$\le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ R _b = 1.4 kΩ		60		100	ns
output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, $R_{b} = 2.7 \text{ k}\Omega$		130		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	$\le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ R _b = 1.4 kΩ	44		110		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	4.0 V, 2.3 V ≤ V _b ≤ 2.7 V, R _b = 2.7 kΩ	44		110		ns
SIp hold time (from SCKp↓)	tksi1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	$\lesssim 5.5 \text{ V}, 2.7 \text{ V} \le V_b \le 4.0 \text{ V},$ R _b = 1.4 kΩ	10		19		ns
Note 2		$\begin{array}{l} 2.7 \ V \leq V_{DD} < \\ C_b = 30 \ pF, \ F \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	10		19		ns
Delay time from SCKp↑ to	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq \\ C_b = 30 \ pF, \ F \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega		10		25	ns
SOp output ^{Note 2}		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ		10		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM number (g = 1)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_{IL}, see the DC characteristics with TTL input buffer selected.

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(6) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		HS (high-speed	d main) Mode	LS (low-speed	l main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксүı	tксү1 ≥ 4/fc∟к	$\begin{array}{l} 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	300		1150		ns
			$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		ns
SCKp high-level tкн1 width		$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	tксү1/2 – 75		tксү1/2 – 75		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2. \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tkcy1/2 - 170		tксү1/2 – 170		ns
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	\leq 5.5 V, 2.7 V \leq V _b \leq 4.0 V, R _b = 1.4 kΩ	tксү1/2 – 12		tксү1/2 – 50		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	tксү1/2 – 18		tксү1/2 – 50		ns
SIp setup time (to SCKp↑) Note 1	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	81		479		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	177		479		ns
SIp hold time (from SCKp↑) _{Note 1}	tksi1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	19		19		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k\Omega	19		19		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_{b} \leq 4.0$ V, R_b = 1.4 k\Omega		100		100	ns
Sop output		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k\Omega		195		195	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, R_b = 1.4 k\Omega	44		110		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} \\ C_b = 30 \ pF, \end{array}$	< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R _b = 2.7 kΩ	44		110		ns
SIp hold time (from SCKp↓) Note 2	tksi1	$\begin{array}{l} 4.0 \ V \leq V_{DD} \\ Cb = 30 \ pF, \end{array}$	≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, Rb = 1.4 k\Omega	19		19		ns
			< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, Rb = 2.7 kΩ	19		19		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1		≤ 5.5 V, 2.7 V $\leq V_b \leq 4.0$ V, Rb = 1.4 k\Omega		25		25	ns
SOP output			< 4.0 V, 2.3 V \leq V _b \leq 2.7 V, Rb = 2.7 kΩ		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.

(Caution and Remarks are listed on the next page.)



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Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_H and V_L, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



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Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



(7) DALI/UART4 mode

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
Transfer rate				fмск/12		fмск/12	bps
		Maximum transfer rate theoretical value HS: fcLk = 32 MHz, fMCk = fcLk LS: fcLk = 8 MHz, fMCk = fcLk		2.6		0.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register mn (SPS4).)

Caution Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.



2.5.2 Serial interface IICA

(1) I²C standard mode

$(T_A = -40 \text{ to } +105^{\circ}C^{\text{ Note } 3}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode: $f_{CLK} \ge 1 \text{ MHz}$	0	100	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		4.7		μs
Hold time ^{Note 1}	thd:sta		4.0		4.0		μs
Hold time when SCLA0 = "L"	t LOW		4.7		4.7		μs
Hold time when SCLA0 = "H"	tнigн		4.0		4.0		μS
Data setup time (reception)	tsu:dat		250		250		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	3.45	μs
Setup time of stop condition	tsu:sto		4.0		4.0		μS
Bus-free time	t BUF		4.7		4.7		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- 2. The maximum value (MAX.) of the:DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω

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(2) I^2C fast mode

$(T_A = -40 \text{ to } +105^{\circ}C^{\text{ Note } 3}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee main) Mode		LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fsc∟	fast mode: fclk \ge 3.5 MHz	0	400	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		0.6		μs
Hold time ^{Note 1}	thd:sta		0.6		0.6		μs
Hold time when SCLA0 = "L"	t∟ow		1.3		1.3		μs
Hold time when SCLA0 = "H"	t HIGH		0.6		0.6		μs
Data setup time (reception)	tsu:dat		100		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	0.9	0	0.9	μs
Setup time of stop condition	tsu:sto		0.6		0.6		μs
Bus-free time	t BUF		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

- **2.** The maximum value (MAX.) of the during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.
- 3. Operating conditions of LS (low-speed main) mode is $T_A = -40$ to +85°C.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



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2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 2.6.1 (1).	See 2.6.1 (3).	See 2.6.1 (4).
ANI16 to ANI19	See 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	See 2.6.1 (1) .		-



(1) When reference voltage (+)= AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = $V_{DD}^{Note 3}$			1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
		10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode	V _{BGR} Note 4			V	
		Temperature sensor output v (HS (high-speed main) mode	Ň	V			

Notes 1. Excludes quantization error (±1/2 LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



- (2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19
- $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}			1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±0.35	%FSR
Integral linearity error ^{Note} 1	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Notes 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AVREFP and VDD	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.



(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{ss} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.1875		39	μs
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	7	0		VDD	V
		ANI16 to ANI19		0		Vdd	V
		Internal reference voltage (HS (high-speed main) mod	e)	V _{BGR} Note 3			V
		Temperature sensor output (HS (high-speed main) mod	0	VTMPS25 ^{Note 3}			V

1	(T _A = –40 to +105°C, 2.7 V ≤ V _{DD} ≤ 5.5 V, V _{SS} =	= 0 V Reference voltage (+) = Vpp	Reference voltage $(-) = V_{SS}$
	$(1A40 \ 10 + 105 \ C, 2.7 \ V \le VDD \le 5.5 \ V, VSS$	- U V, Reference voltage (+) - VDD	, Reference voltage (–) – vss)

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage
 (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

⁽T_A = -40 to +105°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM} = 0 V^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	t CONV	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 2.6.2 Temperature sensor/internal reference voltage characteristics.

When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.



2.6.2 Temperature sensor/internal reference voltage characteristics

		-				
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	VBGRT	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvtmps	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μS

(T_A = -40 to +105°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)



2.6.3 Programmable gain amplifier

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9Vdd/	V
							gain	
Gain error ^{Note 1}		4, 8 times					±1	%
		16 time	s				±1.5	%
		32 time	s				±2	%
Slew rate ^{Note 1}	SRRPGA	edge	•	4, 8 times	4			V/µs
				16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.8			V/µs
				16, 32 times	0.5			V/µs
	SRFPGA	Falling	ag $4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	4, 8 times	3.2			V/µs
		edge		16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.2			V/µs
				16, 32 times	0.5			V/µs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 tim	es		5			μs
		16, 32 t	imes		10			μs

(TA = -40 to +105°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, Vss = AVREFM = 0 V)

Notes 1. When $V_{IPGA} = 0.1V_{DD}/gain$ to $0.9V_{DD}/gain$.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.



2.6.4 Comparator

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		Vdd	V
		СМРСОМ	0.045		0.9Vdd	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3~V \leq V_{\text{DD}} \leq 5.5~V$	1			μs
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	3			μs
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μS

(TA = -40 to +105°C, 2.7 V \leq AVREFP = VDD \leq 5.5 V, Vss = AVREFM = 0 V)

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.
- **Remark** These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.





2.6.5 POR circuit characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.57	V
	VPDR	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width ^{Note}	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).





2.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.97	4.06	4.14	V
voltage			Power supply fall time	3.89	3.98	4.06	V
		VLVD1	Power supply rise time	3.67	3.75	3.82	V
			Power supply fall time	3.59	3.67	3.74	V
		VLVD2	Power supply rise time	3.06	3.13	3.19	V
	VLVD3		Power supply fall time	2.99	3.06	3.12	V
		VLVD3	Power supply rise time	2.95	3.02	3.08	V
			Power supply fall time	2.89	2.96	3.02	V
		VLVD4	Power supply rise time	2.85	2.92	2.97	V
			Power supply fall time	2.79	2.86	2.91	V
		VLVD5	Power supply rise time	2.75	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
Minimum pul	se width	tLW		300			μS
Detection del	ay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{VPDR} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cone	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1,	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage: 2.7 V			2.81	V
mode	VLVD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	2.97	V
			Falling interrupt voltage	2.79	2.86	2.91	V
	VLVD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.08	V
			Falling interrupt voltage	2.89	2.96	3.02	V
	VLVD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.14	V
			Falling interrupt voltage	3.89	3.98	4.06	V

2.6.7 Supply voltage rise inclination characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 32.4 AC Characteristics.



2.7 RAM Data Retention Characteristics

(T_A = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage ^{Note 2}	VDDDR		1.44 ^{Note 1}		5.5	V

- **Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.





2.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.
CPU/peripheral hardware clock frequency	fclĸ	$2.7~V \leq V_{DD} \leq 5.5~V$	1		32
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, T _A = 85°C ^{Note 3}	1,000		
Number of data flash		Retained for 1 year, $T_A = 25^{\circ}C^{Note 3}$		1,000,000	
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, $T_A = 85^{\circ}C^{Note 3}$	100,000		
		Retained for 20 years, $T_A = 85^{\circ}C^{Note 3}$	10,000		

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- 2.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps



Unit MHz

Times

2.10 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	ts∪	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the pin reset ends.).

- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - $t_{su:}$ How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - t_{HD}: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)



3. ELECTRICAL SPECIFICATIONS (M: Industrial applications, $T_A = -40$ to +125°C)

In this chapter, shows the electrical specifications of the target products. Target products (M: Industrial applications): $T_A = -40$ to $+125^{\circ}C$ R5F107xxMxx

- Cautions 1. The RL78/I1A has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. See 2.1 Port Function to 2.2.1 Functions for each product in the RL78/I1A User's Manual.
 - 3. When any of these products are used at 105°C or lower, see 2. ELECTRICAL SPECIFICATIONS $(T_A = -40 \text{ to } +105^{\circ}\text{C}).$



3.1 Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		–0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VI1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	–0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V ₀₁	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	–0.3 to V _{DD} +0.3 ^{Note 2}	V
Analog input voltage	Val1	ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF(+)} +0.3 ^{Notes 2, 3}	V

Absolute Maximum Ratings (T_A = 25°C) (1/2)

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AV_{REF(+)} + 0.3 V in case of A/D conversion target pin.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF (+)}$: + side reference voltage of the A/D converter.
 - **3.** Vss : Reference voltage



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	-40	mA
		Total of all pins	P02, P03, P40, P120	-70	mA
		–170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	-100	mA
	Іон2	Per pin	P20 to P22, P24 to P27	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	40	mA
		Total of all pins	P02, P03, P40, P120	70	mA
		170 mA	P05, P06, P10 to P12, P30, P31, P75 to P77, P147, P200 to P206	100	mA
	IOL2	Per pin	P20 to P22, P24 to P27	1	mA
		Total of all pins]	5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +125	°C
temperature		In flash memory	programming mode	-40 to +105	
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (T_A = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator		1.0		20.0	MHz
XT1 clock frequency (f _{XT}) ^{Note}	Crystal resonator		32	32.768	35	kHz

- **Note** Indicates only permissible oscillator frequency ranges. See **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- **Remark** When using the X1 oscillator and XT1 oscillator, see 5.4 System Clock Oscillator in the RL78/I1A User's Manual.



3.2.2 On-chip oscillator characteristics

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Note 1}	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracy ^{Note 2}		T _A = −20 to 85°C	-1		+1	%
		T _A = -40 to 105°C	-1.5		+1.5	%
		T _A = –40 to 125°C When 16 MHz selected	-2		+2	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

 $(T_A = -40 \text{ to } +125^{\circ}C, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

- **Notes 1.** Frequency can be selected in a high-speed on-chip oscillator. Selected by bits 0 to 3 of option byte (000C2H/010C2H).
 - 2. This indicates the oscillator characteristics only. See AC Characteristics for instruction execution time.
- **Remark** When using the device at an ambient temperature that exceeds T_A = 105°C, the selectable oscillation frequency is 16 MHz max.

3.2.3 PLL characteristics

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
PLL input clock	fpllin	High-speed system clock is selected (f _{MX} = 4 MHz)	3.92	4.00	4.08	MHz
frequency ^{Note}		High-speed on-chip oscillator clock is selected (f_{IH} = 4 MHz)	3.92	4.00	4.08	MHz
PLL output clock frequency ^{Note}	fpll			$f_{\text{PLLIN}} imes 16$		MHz

Note This only indicates the oscillator characteristics. See AC Characteristics for instruction execution time.

Remark When using the device at an ambient temperature that exceeds $T_A = 105^{\circ}C$, only 16 MHz (f_{PLL} × 1/4) can be selected as the CPU operating frequency.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	Іон1	Per pin for P02, P03, P05, P06, P10 to P12,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-3.0 ^{Note 2}	mA
high ^{Note 1}		P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-1.0	mA
		Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-9.0	mA
	(When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-3.0	mA	
	Total of P05, P06, P10 to P12, P30, P31,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-21.0	mA	
		P75 to P77, P147, P200 to P206 (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-6.0	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			-21.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			-9.0	mA
	Іон2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			-0.4	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current,	IOL1	Per pin for P02, P03, P05, P06,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			8.5 ^{Note 2}	mA
low ^{Note 1}	P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	$2.7~V \leq V_{\text{DD}} < 4.0~V$			1.5 ^{Note 2}	mA	
	Total of P02, P03, P40, P120	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			20.0	mA	
	(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			5.0	mA	
		Total of P05, P06, P10 to P12, P30, P31,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			20.0	mA
		P75 to P77, P147, P200 to P206 (When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			10.0	mA
		Total of all pins	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			40.0	mA
		(When duty $\leq 70\%^{\text{Note 3}}$)	$2.7~V \leq V_{\text{DD}} < 4.0~V$			15.0	mA
	IOL2	Per pin for P20 to P22, P24 to P27	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			0.4 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$			1.6	mA

$(T_A = -40 \text{ to } +125^{\circ}C, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0.8Vdd		Vdd	V
	VIH2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	2.1		Vdd	V
			TTL input buffer $3.3 \text{ V} \leq V_{\text{DD}} < 4.0 \text{ V}$	2.0		Vdd	V
			TTL input buffer 2.7 V \leq V_DD $<$ 3.3 V	1.5		Vdd	V
Input voltage, low VIL1	VIL1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120 to P124, P137, P147, P200 to P206, EXCLK, EXCLKS, RESET	Normal input buffer	0		0.2V _{DD}	V
	VIL2	P03, P10, P11	TTL input buffer $4.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$	0		0.8	V
			TTL input buffer $3.3~V \leq V_{\text{DD}} < 4.0~V$	0		0.5	V
			TTL input buffer 2.7 V \leq V_{DD} < 3.3 V	0		0.32	V

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Caution The maximum value of VIH of pins P02, P10 to P12 is VDD, even in the N-ch open-drain mode.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -3.0 \ \text{mA} \end{array}$	Vdd - 0.7			V
V _{OH2}		P200 to P206	$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OH1}} = -1.0 \ \text{mA} \end{array}$	Vdd - 0.5			V
	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Ioh2 = -100 μ A	Vdd - 0.5			V	
low F	Vol1	P31, P40, P75 to P77, P120, P147,	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 8.5 \ mA \end{array} \end{array} \label{eq:DD}$			0.7	V
			$4.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol1 = 4.0 mA			0.4	V
		$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ I_{\text{OL1}} = 1.5 \ mA \end{array} \end{array} \label{eq:DD}$			0.4	V	
	Vol2	P20 to P22, P24 to P27	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ Iol2 = 400 μ A			0.4	V

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)

Caution P02, P10 to P12 do not output high level in N-ch open-drain mode.



Items	Symbol	Condition	IS		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	VI = VDD				1	μA
	Іцн2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	IL1L1	P02, P03, P05, P06, P10 to P12, P20 to P22, P24 to P27, P30, P31, P40, P75 to P77, P120, P137, P147, P200 to P206, RESET	Vi = Vss				-1	μA
	ILIL2	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)		In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P02, P03, P05, P06, P10 to P12, P30, P31, P40, P75 to P77, P120, P147, P200 to P206	VI = Vss, In input port		10	20	100	kΩ

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, V_SS = 0 V)



3.3.2 Supply current characteristics

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	f⊪ = 16 MHz ^{Note 3}	V _{DD} = 5.0 V		2.9	4.8	mA
Current Note 1		mode	speed main) mode ^{Note 5}		V _{DD} = 3.0 V		2.9	4.8	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
			speed main) mode ^{Note 5}	V _{DD} = 5.0 V	Resonator connection		3.3	5.7	mA
			mode	f _{MX} = 20 MHz ^{Note 2} ,	Square wave input		3.2	5.6	mA
				V _{DD} = 3.0 V	Resonator connection		3.3	5.7	mA
				f _{MX} = 10 MHz ^{Note 2} ,	Square wave input		2.0	3.3	mA
				V _{DD} = 5.0 V	Resonator connection		2.0	3.3	mA
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Square wave input		2.0	3.3	mA
			V _{DD} = 3.0 V	Resonator connection		2.0	3.3	mA	
		HS (high-	fiH = 4 MHz ^{Note 3}	V _{DD} = 5.0 V		3.3	6.5	mA	
		speed main) mode ^{Note 5}	fpll = 64 MHz, fclк = 16 MHz	V _{DD} = 3.0 V		3.3	6.5	mA	
			Subsystem clock operation	fs∪B = 32.768 kHz ^{Note 4} T _A = −40°C	Square wave input		4.2	6.0	μA
					Resonator connection		4.4	6.2	μA
				f _{SUB} = 32.768 kHz ^{Note 4} T _A = +25°C	Square wave input		4.2	6.0	μA
					Resonator connection		4.4	6.2	μA
				fsue = 32.768 kHz ^{Note 4}	Square wave input		4.3	7.2	μA
				T _A = +50°C	Resonator connection		4.5	7.4	μA
				fsuв = 32.768 kHz ^{Note 4}	Square wave input		4.4	8.1	μA
				T _A = +70°C	Resonator connection		4.6	8.3	μA
				fsub = 32.768 kHz ^{Note 4}	Square wave input		5.2	11.4	μA
				T _A = +85°C	Resonator connection		5.4	11.6	μA
			fsub = 32.768 kHz ^{Note 4}	Square wave input		6.9	20.8	μA	
			T _A = +105°C	Resonator connection		7.1	21.0	μA	
			fsuв = 32.768 kHz ^{Note 4}	Square wave input		11.1	51.2	μA	
				T _A = +125°C	Resonator connection		11.3	51.4	μA

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



< R >

- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main) modes.
 - •The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.
 In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 20 MHz

- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. file: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{ V}_{\text{SS}} = 0 \text{ V}) (2/2)$

	Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
<r></r>	Supply current Note 1	IDD2Note 2	HALT mode	HS (high- speed main) mode ^{Note 6}	fi⊢ = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.0	mA
						V _{DD} = 3.0 V		0.50	2.0	mA
				HS (high- speed main) mode ^{Note 6}	f_{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.40	2.2	mA
						Resonator connection		0.50	2.3	mA
					f_{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.40	2.2	mA
						Resonator connection		0.50	2.3	mA
					f_{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.24	1.22	mA
						Resonator connection		0.30	1.28	mA
					f_{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.24	1.22	mA
						Resonator connection		0.30	1.28	mA
				HS (high- speed main) mode ^{Note 6}	$f_{\text{IH}} = 4 \text{ MHz}^{\text{Note 4}}$ $f_{\text{PLL}} = 64 \text{ MHz}, f_{\text{CLK}} = 16 \text{ MHz}$	V _{DD} = 5.0 V		0.95	3.7	mA
						V _{DD} = 3.0 V		0.95	3.7	mA
				Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$ $T_A = -40^{\circ}\text{C}$	Square wave input		0.28	0.70	μA
						Resonator connection		0.47	0.89	μA
					fs∪b = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.33	0.70	μA
						Resonator connection		0.52	0.89	μA
					f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	1.90	μA
						Resonator connection		0.60	2.09	μA
					f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.54	2.80	μA
						Resonator connection		0.73	2.99	μA
					fsub = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.27	6.10	μA
						Resonator connection		1.46	6.29	μA
					fsub = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		3.04	15.5	μA
						Resonator connection		3.23	15.7	μA
					fsub = 32.768 kHz ^{Note 5} T _A = +125°C	Square wave input		7.20	45.2	μA
						Resonator connection		7.53	45.5	μA
<r></r>		Ісоз	STOP mode Note 7	$T_A = -40^{\circ}C$				0.18	0.50	μA
				T _A = +25°C				0.23	0.50	μA
				T _A = +50°C				0.27	1.70	μA
				T _A = +70°C				0.44	2.60	μA
				T _A = +85°C				1.17	5.90	μA
				T _A = +105°C				2.94	15.3	μA
				T _A = +125°C	Γ _A = +125°C			7.14	45.1	μA

(Notes and Remarks are listed on the next page.)


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- **Notes 1.** Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.

• The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- 2. During HALT instruction execution by flash memory.
- 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- **4.** When high-speed system clock and subsystem clock are stopped.
- **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ @1 MHz to 20 MHz

- 7. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C



Parameter	Symbol		Conditions	3	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	_{FIL} Note 1					0.20		μA
RTC operating current	IRTC Notes 1, 2, 3					0.02		μA
12-bit interval timer operating current	ı⊤ Notes 1, 2, 4					0.02		μA
Watchdog timer operating current	WDT Notes 1, 2, 5	f⊾ = 15 kHz				0.22		μA
A/D converter operating current	ADC Notes 1, 6		When conversion at Normal mode, AVREFP = VDD = 5.0 V maximum speed Image: Conversion of the speed				1.7	mA
A/D converter reference voltage current	ADREF ^{Note 1}					75.0		μA
Temperature sensor operating current	TMPS ^{Note 1}					75.0		μA
LVD operating current	ILVD ^{Notes 1, 7}					0.08		μA
Self-programming operating current	FSP Notes 1, 8					2.5	12.2	mA
Programmable	PGA ^{Note 9}			AV _{REFP} = V _{DD} = 5.0 V		0.21	0.37	mA
gain amplifier operating current				$AV_{REFP} = V_{DD} = 3.0 V$		0.18	0.35	mA
Comparator	CMP ^{Note 10}		parator channel is	AV _{REFP} = V _{DD} = 5.0 V		41.4	74	μA
operating current		operating		$AV_{REFP} = V_{DD} = 3.0 V$		37.2	71	μA
	IVREF	When one inter	nal reference voltage	$AV_{REFP} = V_{DD} = 5.0 V$		14.8	31	μA
		circuit is operati	ng	$AV_{REFP} = V_{DD} = 3.0 V$		8.9	24	μA
Programmable	IIREF ^{Note 11}			$AV_{REFP} = V_{DD} = 5.0 V$		3.2	6.1	μA
gain amplifier/ comparator reference current source				AV _{REFP} = V _{DD} = 3.0 V		2.9	4.9	μA
BGO operating current	BGO ^{Note 12}					2.50	12.2	mA
SNOOZE	ISNOZ ^{Note 1}	A/D converter	The mode is perform	ned ^{Note 13}		0.50	1.10	mA
operating current		operation	The A/D conversion Normal mode, AVRE	operations are performed, =P = V _{DD} = 5.0 V		1.20	2.17	mA
		Simplified SPI (CSI)/UART operation			0.70	1.27	mA

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

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(Notes and Remarks are listed on the next page.)



Notes 1. Current flowing to the VDD.

- 2. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operating mode or in HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the XT1 oscillator and f_{IL} operating current). The current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IWDT, when the watchdog timer is operating.
- **6.** Current flowing only to the A/D converter. The supply current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, when the A/D converter is operating in operating mode or in HALT mode.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing during self-programming operation.
- **9.** Current flowing only to the programmable gain amplifier. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IPGA, when the programmable gain amplifier is operating in operating mode or in HALT mode.
- **10.** Current flowing only to the comparator. The supply current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and ICMP, when the comparator is operating.
- **11.** This is the current required to flow to V_{DD} pin of the current circuit that is used as the programmable gain amplifier and the comparator.
- 12. Current flowing only during data flash rewrite.
- 13. See 21.3.3 SNOOZE mode in the RL78/I1A User's Manual for shift time to the SNOOZE mode.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - 4. Temperature condition of the TYP. value is T_A = 25°C
 - 5. Example of calculating current value when using programmable gain amplifier and comparator.
 - Examples 1) TYP. operating current value when three comparator channels, one internal reference voltage generator, and PGA are operating (when AV_{REFP} = V_{DD} = 5.0 V)

ICMP × 3 + IVREF + IPGA + IIREF

 $= 41.4 \ [\mu A] \times 3 + 14.8 \ [\mu A] \times 1 + 210 \ [\mu A] + 3.2 \ [\mu A] \\ = 352.2 \ [\mu A]$

Examples 2) TYP. operating current value when using two comparator channels, without using internal reference voltage generator (when AV_{REFP} = V_{DD} = 5.0 V)

 $I_{CMP} \times 2 + I_{IREF}$ = 41.4 [μ A] × 2 + 3.2 [μ A] = 86.0 [μ A]



3.4 AC Characteristics

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Items	Symbol		Cond	itions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсү	Main system clock (f _{MAIN}) operation	HS (high-s	peed r	nain) mode	0.05		1	μs
		Subsystem c	lock (fsua)	opera	ation	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-s main) mod	•	T _A = -40 to +105°C	0.05		1	μs
External system clock frequency	f _{EX}					1.0		20.0	MHz
	fexs					32		35	kHz
External system clock input high-	texH, texL				24			ns	
level width, low-level width	texns, texls				13.7			μs	
TI03, TI05, TI06, TI07 input high- level width, low-level width	tтıн, tтı∟					2/fмск+10			ns
T003, T005, T006, TKB000,	fто	HS (high-speed main)		4.0 \	$I \leq V_{\text{DD}} \leq 5.5 \text{ V}$			5	MHz
TKBO01, TKBO10, TKBO11, TKBO20, TKBO21, TKCO00 to TKCO05 output frequency (When duty = 50%)		mode		2.7 \	$I \leq V_{DD} < 4.0 V$			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0, INTP3 INTP9 to INT INTP20 to IN	P11,	2.7 \	$V \le V_{DD} \le 5.5 V$	1			μs
RESET low-level width	trsl					10			μs

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKS0n bit of timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))



Minimum Instruction Execution Time during Main System Clock Operation

TCY vs VDD (HS (high-speed main) mode)



AC Timing Test Points



External System Clock Timing





TI/TO Timing





3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit 0, 4 (UART0, UART1, CSI00, DALI/UART4)

(1) During communication at same potential (UART mode)

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		Conditions HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate ^{Note 1}					fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: 20 MHz ($2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$)

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)

2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))



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(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol		Conditions		Conditions HS (high-speed main) Mode		,	Unit
				MIN.	MAX.			
SCKp cycle time	tkCY1	tκcγ1 ≥ 4/fclκ	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	250		ns		
			$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	500		ns		
SCKp high-/low-level width	t кн1,	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 – 20		ns		
	t ĸ∟1	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		tксү1/2 – 40		ns		
SIp setup time (to SCKp↑) ^{Note 1}	tsik1	$4.0~V \leq V_{\text{DD}} \leq 5.5$	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$			ns		
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$		80		ns		
SIp hold time (from SCKp↑) ^{Note 2}	t _{KSI1}			40		ns		
Delay time from SCKp↓ to SOp output ^{Note 3}	tkso1	C = 30 pF ^{Note 4}			80	ns		

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 - g: PIM and POM number (g = 1)
 - 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))



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(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions			HS (high-speed main) Mode	
				MIN.	MAX.	
SCKp cycle time ^{Note 5}	t ксү2	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	fмск ≤ 20 MHz	6/fмск		ns
		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	16 MHz < fмск	8/fмск		ns
			fмск ≤ 16 MHz	6/fмск		ns
SCKp high-/low-level width	tкн2, tкL2			tксү2/2		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsık2			1/fмск+40		ns
SIp hold time (from SCKp↑) ^{Note 2}	tksi2			1/fмск+60		ns
Delay time from SCKp↓ to SOp output ^{Note 3}	tĸso2	C = 30 pF ^{Note 4}			2/fмск+80	ns

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)
 - 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00))





Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Conditions				Unit
					MIN.	MAX.	
Transfer rate		Reception	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \ V \end{array}$			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps
			$\begin{array}{l} 2.7 \ V \leq V_{\text{DD}} < 4.0 \ V, \\ 2.3 \ V \leq V_{\text{b}} \leq 2.7 \ V \end{array}$			fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		3.3	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)



(4) Communication at different potential (2.5 V, 3 V) (UART mode) (2/2) (T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V)

Parameter	Symbol		Conditions			HS (high-speed main) Mode		
					MIN.	MAX.		
Transfer rate		Transmission	$4.0~V \leq V_{\text{DD}} \leq 5.5~V,$			Note 1	bps	
		$2.7~V \leq V_b \leq 4.0~V$	$2.7~V \leq V_b \leq 4.0~V$	$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.8 ^{Note 2}	Mbps
			$2.7~V \leq V_{\text{DD}} < 4.0~V,$			Note 3	bps	
			$2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 ^{Note 4}	Mbps	

Notes 1. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
[bps]
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 1** above to calculate the maximum transfer rate under conditions of the customer.
- **3.** The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq Vpd < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. See **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remarks 1.** $R_b[\Omega]$: Communication line (TxDq) pull-up resistance,

Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage

- **2.** q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)
- **3.** fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03))



UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $V_b[V]$: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 0, 1)



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(5) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +125°C, 2.7 V \leq V_DD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	HS (high-sp Mod	-	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fclк		600		ns
			$\label{eq:VDD} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1000		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ F \end{array}$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, Rb = 1.4 k\Omega	tксү1/2 – 80		ns
		$\begin{array}{l} 2.7 \ V \leq V_{DD} < \\ C_b = 30 \ pF, \ F \end{array}$	\times 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω	tксү1/2 – 170		ns
SCKp low-level width	tĸL1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	≤ 5.5 V, 2.7 V \leq Vb ≤ 4.0 V, Rb = 1.4 k\Omega	tkcy1/2 - 28		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	tkcy1/2 - 40		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsikı	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	160		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω	250		ns
SIp hold time (from SCKp↑) ^{Note 1}		$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	40		ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω	40		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega		160	ns
		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω		250	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsik1	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	80		ns
		$2.7 V \le V_{DD} < C_b = 30 \text{ pF, F}$: 4.0 V, 2.3 V \leq Vb \leq 2.7 V, Rb = 2.7 k Ω	80		ns
SIp hold time (from SCKp↓) ^{Note 2}	tksii	$\begin{array}{l} 4.0 \ V \leq V_{\text{DD}} \leq \\ C_{\text{b}} = 30 \ \text{pF}, \ \text{F} \end{array}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega	40		ns
、 ,		$2.7 \text{ V} \le \text{V}_{\text{DD}} < C_{\text{b}} = 30 \text{ pF}, \text{ F}$: 4.0 V, 2.3 V \leq V_b \leq 2.7 V, R_b = 2.7 k Ω	40		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tкso1 4.	$4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF}, \text{ F}$	$\lesssim 5.5$ V, 2.7 V \leq Vb \leq 4.0 V, Rb = 1.4 k\Omega		80	ns
			$4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$		80	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

(Caution and Remarks are listed on the next page.)



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Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)



- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),
 g: PIM and POM number (g = 1)



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- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 1)



(6) DALI/UART4 mode

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate				fмск/12	bps
		Maximum transfer rate theoretical value fcLK = 20 MHz, fMCK = fcLK		1.6	Mbps

Remark fmck: Operation clock frequency of DALI/UART.

(Operation clock to be set by the serial clock select register 4 (SPS4).)



3.5.2 Serial interface IICA

(1) I²C standard mode

$(T_A = -40 \text{ to } +125^{\circ}C, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fsc∟	Standard mode: $f_{CLK} \ge 1 \text{ MHz}$	0	100	kHz
Setup time of restart condition	tsu:sta		4.7		μS
Hold time ^{Note 1}	thd:sta		4.0		μs
Hold time when SCLA0 = "L"	t∟ow		4.7		μS
Hold time when SCLA0 = "H"	tніgн		4.0		μs
Data setup time (reception)	tsu:dat		250		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	μS
Setup time of stop condition	tsu:sto		4.0		μs
Bus-free time	t BUF		4.7		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω

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(2) I²C fast mode

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLA0 clock frequency	fsc∟	fast mode: fcLK≥ 3.5 MHz	0	400	kHz
Setup time of restart condition	tsu:sta		0.6		μs
Hold time ^{Note 1}	thd:sta		0.6		μs
Hold time when SCLA0 = "L"	t∟ow		1.3		μs
Hold time when SCLA0 = "H"	tнigн		0.6		μs
Data setup time (reception)	tsu:dat		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	0.9	μs
Setup time of stop condition	tsu:sto		0.6		μs
Bus-free time	t BUF		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

fast mode:

 C_b = 320 pF, R_b = 1.1 k Ω



IICA serial transfer timing



Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
Input channel	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI2, ANI4 to ANI7	See 3.6.1 (1).	See 3.6.1 (3).	See 3.6.1 (4) .
ANI16 to ANI19	See 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	See 3.6.1 (1) .		_



(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target ANI pin: ANI2, ANI4 to ANI7, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le AV_{REFP} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V}, \text{ Reference voltage (+)} = AV_{REFP}, \text{ Reference voltage (-)} = AV_{REFM} = 0 \text{ V})$

Parameter	Symbol	Condition	IS	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±3.5	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI2, ANI4 to ANI7	$2.7~V \leq V \text{DD} \leq 5.5~V$	3.4		39	μs
		10-bit resolution	$3.6~V \leq V \text{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \le V_{DD} \le 5.5~V$	3.8		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.25	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±1.5	LSB
Analog input voltage	VAIN	ANI2, ANI4 to ANI7		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) mode)		VBGR ^{Note 4}		V
		Temperature sensor output v (HS (high-speed main) mode	0	N	V⊤MPS25 ^{Note}	4	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI19

(TA = -40 to +125°C, 2.7 V \leq AV _{REFP} \leq V _{DD} \leq 5.5 V, V _{SS} = 0 V, Reference voltage (+) = AV _{REFP} , AV _{REFP} , AV _{REFP} , AV _{REFP} , AV	ŧ
voltage (–) = AV _{REFM} = 0 V)	

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}			1.2	±5.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target ANI pin : ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} < 5.5~V$	3.4		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Efs	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution AV _{REFP} = V _{DD} ^{Note 3}				±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI19		0		AV _{REFP}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.2\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.



(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19, internal reference voltage, and temperature sensor output voltage

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI2, ANI4 to ANI7, ANI16 to ANI19	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.4		39	μs
Conversion time	t CONV	10-bit resolution	$3.6~V \leq V_{\text{DD}} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.8		39	μs
		main) mode)					
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution				±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution				±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
Differential linearity error	DLE	10-bit resolution				±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI2, ANI4 to ANI7	7	0		Vdd	V
		ANI16 to ANI19		0		Vdd	V
		Internal reference voltage (HS (high-speed main) mode)		V _{BGR} Note 3			V
		Temperature sensor output (HS (high-speed main) mod	0	١	/TMPS25 Note	3	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- **2.** This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI0, ANI2, ANI4 to ANI7, ANI16 to ANI19

(T_A = -40 to +125°C, 2.7 V \leq V_{DD} \leq 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR}^{Note 3}, Reference voltage (-) = AV_{REFM} ^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv	8-bit resolution	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution			±2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	VAIN		0		$V_{\text{BGR}}^{\text{Note 3}}$	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See 3.6.2 Temperature sensor/internal reference voltage characteristics.

4. When reference voltage (–) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM}.

Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM}.

3.6.2 Temperature sensor/internal reference voltage characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/C
Operation stabilization wait time	tamp		5			μs

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)



3.6.3 Programmable gain amplifier

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±5	±10	mV
Input voltage range	VIPGA				0		0.9Vdd/	V
							gain	
Gain error ^{Note 1}		4, 8 tim	es				±1	%
		16 time	s				±1.5	%
		32 times					±2	%
Slew rate ^{Note 1}	SRrpga	Rising edge	$4.0~V \le V_{\text{DD}} \le 5.5~V$	4, 8 times	4			V/µs
				16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.8			V/µs
				16, 32 times	0.5			V/µs
	SRFPGA	Falling	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	4, 8 times	3.2			V/µs
		edge		16, 32 times	1.4			V/µs
			$2.7~V \leq V_{\text{DD}} < 4.0~V$	4, 8 times	1.2			V/µs
				16, 32 times	0.5			V/µs
Operation stabilization wait time ^{Note 2}	t PGA	4, 8 times		5			μs	
		16, 32 times		10			μs	

$(T_A = -40 \text{ to } +125^{\circ}\text{C}, 2.7 \text{ V} \le \text{AV}_{\text{REFP}} = \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Notes 1. When VIPGA = 0.1VDD/gain to 0.9VDD/gain.

2. Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

Remark These characteristics apply when AVREFM is selected as GND of the PGA by using the CVRVS1 bit.



3.6.4 Comparator

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOCMP			±5	±40	mV
Input voltage range	VICMP	CMP0P to CMP5P	0		Vdd	V
		СМРСОМ	0.045		0.9Vdd	V
Internal reference voltage deviation	ΔV_{IREF}	CmRVM register values: 7FH to 80H (m = 0 to 2)			±2	LSB
		Other than above			±1	LSB
Response time	tcr, tcr	Input amplitude = ±100 mV		70	150	ns
Operation stabilization wait time ^{Note 1}	tсмр	$3.3~V \leq V_{\text{DD}} \leq 5.5~V$	1			μS
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}$	3			μS
Reference voltage stabilization wait time	tvr	CVRE: 0 to 1 ^{Note 2}	10			μs

- **Notes 1.** Time required until a state is entered where the DC and AC specifications of the comparator are satisfied after the operation of the comparator has been enabled (CMPnEN bit = 1: n = 0 to 5)
 - Enable comparator output (CnOE bit = 1; n = 0 to 5) after enabling operation of the internal reference voltage generator (by setting the CVREm bit to 1; m = 0 to 2) and waiting for the operation stabilization time to elapse.
- **Remark** These characteristics apply when AV_{REFP} is selected as the power supply source of the internal reference voltage by using the CVRVS0 bit, and when AV_{REFM} is selected as GND of the internal reference voltage by using the CVRVS1 bit.





3.6.5 POR circuit characteristics

(T_A = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.45	1.51	1.62	V
	VPDR	Power supply fall time	1.44	1.50	1.61	V
Minimum pulse width ^{Note}	TPW		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode (TA = -40 to +125°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	VLVD0	Power supply rise time	3.97	4.06	4.25	V
voltage	oltage		Power supply fall time	3.89	3.98	4.15	V
		VLVD1	Power supply rise time	3.67	3.75	3.93	V
			Power supply fall time	3.59	3.67	3.83	V
		VLVD2	Power supply rise time	3.06	3.13	3.28	V
			Power supply fall time	2.99	3.06	3.20	V
		VLVD3	Power supply rise time	2.95	3.02	3.17	V
			Power supply fall time	2.89	2.96	3.09	V
		VLVD4	Power supply rise time	2.85	2.92	3.07	V
			Power supply fall time	2.79	2.86	2.99	V
		VLVD5	Power supply rise time	2.75	2.81	2.95	V
			Power supply fall time	2.70	2.75	2.88	V
Minimum pu	ulse width	tLw		300			μs
Detection de	elay time					300	μs



LVD Detection Voltage of Interrupt & Reset Mode ($T_A = -40$ to +125°C, $V_{PDR} \le V_{DD} \le 5.5$ V, $V_{SS} = 0$ V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1,	falling reset voltage: 2.7 V	2.70	2.75	2.88	V
mode	VLVD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.85	2.92	3.07	V
			Falling interrupt voltage	2.79	2.86	2.99	V
	VLVD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
			Falling interrupt voltage	2.89	2.96	3.09	V
	VLVD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.97	4.06	4.25	V
			Falling interrupt voltage	3.89	3.98	4.15	V

3.6.7 Supply voltage rise inclination characteristics

(T_A = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage rise	SVDD				54	V/ms

Caution Keep the internal reset status by using the LVD circuit or an external reset signal until VDD rises to within the operating voltage range shown in 33.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

(T_A = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage ^{Note 2}	VDDDR		1.47 ^{Note 1}		5.5	V

- **Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Caution When CPU is operated at the voltage of out of the operation voltage range, RAM data is not retained. Therefore, set STOP mode before the supplied voltage is below the operation voltage range.





3.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fськ	$2.7~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites ^{Notes 1, 2, 3}	Cerwr	Retained for 20 years, $T_A = 85^{\circ}C^{Note 3, 4}$	1,000			Times
Number of data flash		Retained for 1 year, $T_A = 25^{\circ}C^{Note 3, 4}$		1,000,000		
rewrites ^{Notes 1, 2, 3}		Retained for 5 years, $T_A = 85^{\circ}C^{Note 3, 4}$	100,000			
		Retained for 20 years, $T_A = 85^{\circ}C^{Note 3, 4}$	10,000			

(TA = -40 to +105°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 - 4. These are the average temperature of during the retainment.

3.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115.2 k		1 M	bps



3.10 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	ts∪	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after a reset ends (except soft processing time)	tно	POR and LVD reset must end before the external reset ends.	1			ms

(TA = -40 to +125°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the pin reset ends.).
- <3> The TOOL0 pin is set to the high level.
- <4> Complete the baud rate setting by UART reception.
- **Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
 - tsu: How long from when the TOOL0 pin is placed at the low level until an external reset ends
 - thd: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)



4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1076CGSP#V0, R5F1076CGSP#X0, R5F1076CMSP#V0, R5F1076CMSP#X0



NOTE

1.Dimensions "%1" and "%2" do not include mold flash.

2.Dimension " \times 3" does not include trim offset.

	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
Е	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 + 0.10 - 0.05
С	$0.15 \pm 0.05 - 0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

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4.2 30-pin Products

R5F107ACGSP#V0, R5F107AEGSP#V0, R5F107ACGSP#X0, R5F107AEGSP#X0, R5F107ACMSP#V0, R5F107AEMSP#V0, R5F107ACMSP#X0, R5F107AEMSP#X0

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18



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U

0.6±0.15



4.3 38-pin Products

R5F107DEGSP#V0, R5F107DEGSP#X0, R5F107DEMSP#V0, R5F107DEMSP#X0



NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

Α	12.30±0.10
В	0.30
С	0.65 (T.P.)
D	$0.32\substack{+0.08 \\ -0.07}$
E	0.125±0.075
F	2.00 MAX.
G	1.70±0.10
Н	8.10±0.20
I	6.10±0.10
J	1.00±0.20
К	$0.17\substack{+0.08\\-0.07}$
L	0.50
М	0.10
Ν	0.10
Р	$3^{\circ}^{+7^{\circ}}_{-3^{\circ}}$
Т	0.25(T.P.)
U	0.60±0.15
V	0.25 MAX.
W	0.15 MAX.

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Revision History

RL78/I1A Datasheet

			Description
Rev.	Date	Page	Summary
3.20	Sep 29, 2017	p.1	Modification of description in 1.1 Features
		p.59	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes
		p.102	Modification of figure in 3.10 Timing of Entry to Flash Memory Programming Modes
		p.103	Modification of figure in 4.1 20-pin Products
3.30	Mar 30, 2023	p.1	Modification of CSI to Simplified SPI (CSINote1) in 1.1 Features
		p.2	Addition of Note 1 in 1.1 Features
		p.12	Modification of CSI to Simplified SPI (CSI) in 1.6 Outline of Functions
		p.25	Modification of Note 1 in 2.3.2 Supply current characteristics
			Modification of Note 4 in 2.3.2 Supply current characteristics
		p.26	Modification of Note 7 to Note 6 in 2.3.2 Supply current characteristics
			Deletion of Note 6 in 2.3.2 Supply current characteristics
			Modification of Note 8 to Note 7 in 2.3.2 Supply current characteristics
		p.27	Modification of Note 1 in 2.3.2 Supply current characteristics
			Modification of Note 6 in 2.3.2 Supply current characteristics
			Deletion of Note 6 in 2.3.2 Supply current characteristics
			Modification of Note 7 to Note 6 in 2.3.2 Supply current characteristics
			Modification of Note 8 to Note 7 in 2.3.2 Supply current characteristics
		p.28	Modification of CSI to Simplified SPI (CSI) in 2.3.2 Supply current characteristics
		p.34	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.35	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.36	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.40	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.41	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.42	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.43	Modification of CSI to Simplified SPI (CSI) in 2.5 Peripheral Functions Characteristics
		p.45	Modification of wait to clock stretch in 2.5.2 Serial interface IICA
		p.46	Modification of wait to clock stretch in 2.5.2 Serial interface IICA
		p.71	Modification of Note 1 in 3.3.2 Supply current characteristics
			Modification of Note 4 in 3.3.2 Supply current characteristics
		p.72	Modification of Note 7 to Note 6 in 3.3.2 Supply current characteristics
			Deletion of Note 6 in 3.3.2 Supply current characteristics
			Modification of Note 8 to Note 7 in 3.3.2 Supply current characteristics
		p.73	Modification of Note 1 in 3.3.2 Supply current characteristics
			Modification of Note 5 in 3.3.2 Supply current characteristics
			Deletion of Note 6 in 3.3.2 Supply current characteristics
			Modification of Note 7 to Note 6 in 3.3.2 Supply current characteristics
			Modification of Note 8 to Note 7 in 3.3.2 Supply current characteristics
		p.74	Modification of CSI to Simplified SPI (CSI) in 3.3.2 Supply current characteristics
		p.80	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics
		p.81	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics
		p.82	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics
		p.86	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics
		p.87	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics
		p.88	Modification of CSI to Simplified SPI (CSI) in 3.5 Peripheral Functions Characteristics

			Description		
Rev.	Date	Page	Summary		
		p.90	Modification of wait to clock stretch in 3.5.2 Serial interface IICA		
3.30	Mar 30, 2023	p.91	Modification of wait to clock stretch in 3.5.2 Serial interface IICA		

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The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power is supplied until the power reaches the level at which reseting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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